

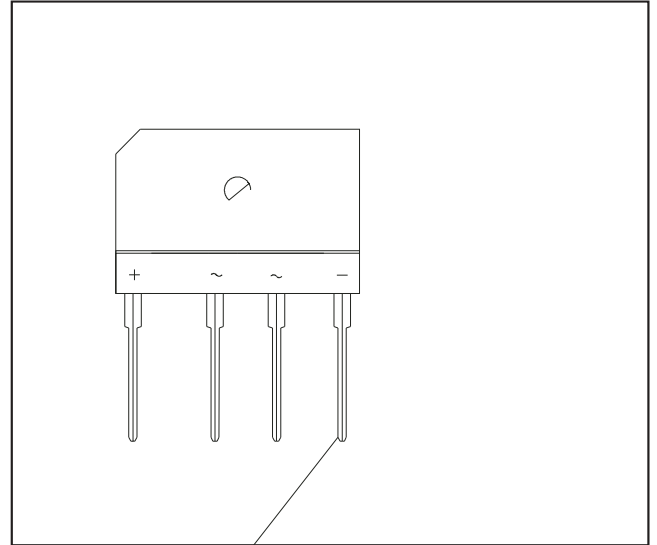
KBJ SILICON BRIDGE RECTIFIER

REVERSE VOLTAGE: 50V --- 1000V CURRENT: 2.0A

FEATURES

MECHANICAL DATA

Mounting position: Any



MAXIMUM RATINGS AND CHARACTERISTICS

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		KBJ 2A	KBJ 2B	KBJ 2D	KBJ 2G	KBJ 2J	KBJ 2K	KBJ 2M	UNITS
Maximum recurrent peak reverse voltage	V_{RRM}	50	100	200	400	600	800	1000	V
Maximum RMS voltage	V_{RMS}	35	70	140	280	420	560	700	V
Maximum DC blocking voltage	V_{DC}	50	100	200	400	600	800	1000	V
Maximum average forward Output current @ $T_A=50^\circ\text{C}$	$I_{F(AV)}$	2.0							A
Peak forward surge current 8.3ms single half-sine-wave superimposed on rated load	I_{FSM}	50.0							A
Maximum instantaneous forward voltage at 1.0 A	V_F	1.0							V
Maximum reverse current @ $T_A=25^\circ\text{C}$ at rated DC blocking voltage @ $T_A=100^\circ\text{C}$	I_R	10.0 1.0							A mA
Typical junction capacitance per element	C_J	45							pF
Typical thermal resistance	R_{JC}	2.2							$^\circ\text{C}/\text{W}$
Operating junction temperature range	T_J	- 55 ---- + 125							$^\circ\text{C}$
Storage temperature range	T_{STG}	- 55 ---- + 150							$^\circ\text{C}$

NOTES:1. Measured at 1.0MHz and applied reverse voltage of 4.0V DC

2. Device mounted on 300mm X 300mm X 1.6mm cu Plate heatsink.

100

10

1.0

0.1

.01

.2

.4

.6

.8

1.0

1.2

1.4